BAT54T1G

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 Volts (Typ) @ I_F = 10 mAdc
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 125°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Power Dissipation, FR−5 Board (Note 1) @ T_A = 25°C Derate above 25°C	P_F	 400 3.2	 mW mW/°C
Thermal Resistance, Junction−to−Case	$R_{\theta JL}$	174	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	492	°C/W
Forward Current (DC)	I_F	200 Max	mA
Non−Repetitive Peak Forward Current t_p < 10 msec	I_{FSM}	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I_{FRM}	300	mA
Junction Temperature	T_J	−55 to 125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.062 in.

ON Semiconductor®

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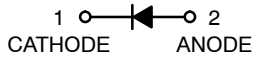
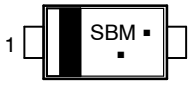
30 VOLT SCHOTTKY BARRIER DETECTOR AND SWITCHING DIODES



SOD−123
CASE 425
STYLE 1

MARKING DIAGRAM



SB = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

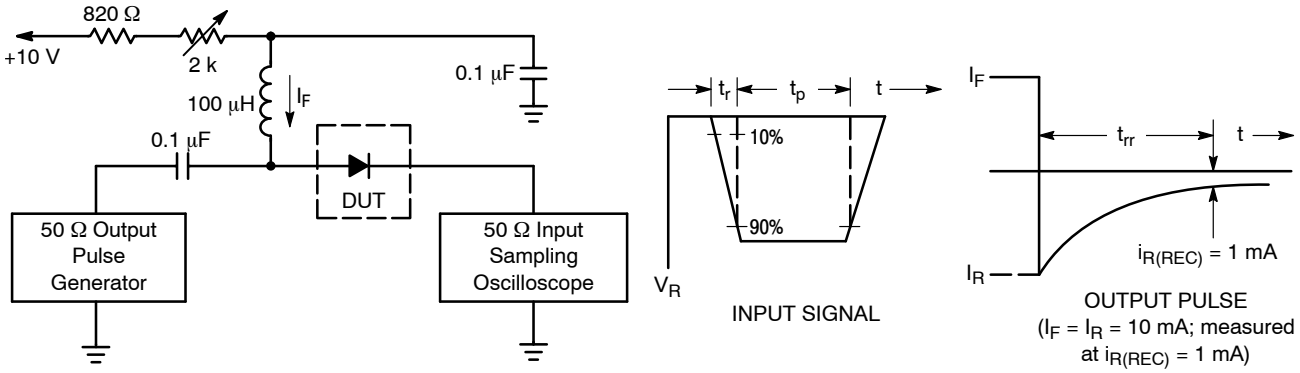
ORDERING INFORMATION

Device	Package	Shipping†
BAT54T1G	SOD−123 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μA)	$V_{(BR)R}$	30	–	–	V
Total Capacitance (V_R = 1.0 V, f = 1.0 MHz)	C_T	–	7.6	10	pF
Reverse Leakage (V_R = 25 V)	I_R	–	0.5	2.0	μAdc
Forward Voltage (I_F = 0.1 mAdc)	V_F	–	0.22	0.24	Vdc
Forward Voltage (I_F = 30 mAdc)	V_F	–	0.41	0.5	Vdc
Forward Voltage (I_F = 100 mAdc)	V_F	–	0.52	0.8	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc, Figure 1)	t_{rr}	–	–	5.0	ns
Forward Voltage (I_F = 1.0 mAdc)	V_F	–	0.29	0.32	Vdc
Forward Voltage (I_F = 10 mAdc)	V_F	–	0.35	0.40	Vdc



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

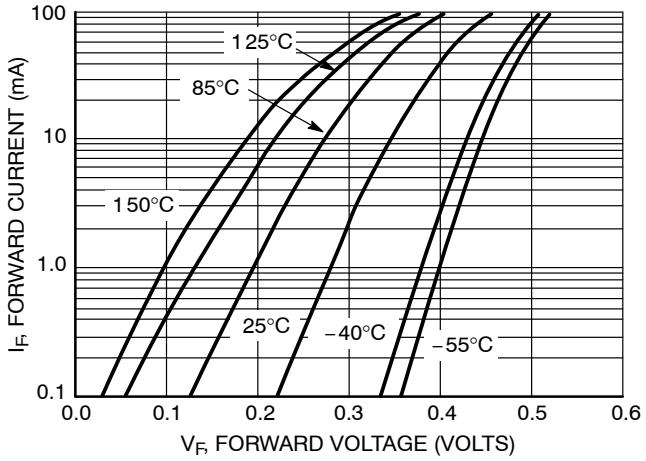


Figure 2. Forward Voltage

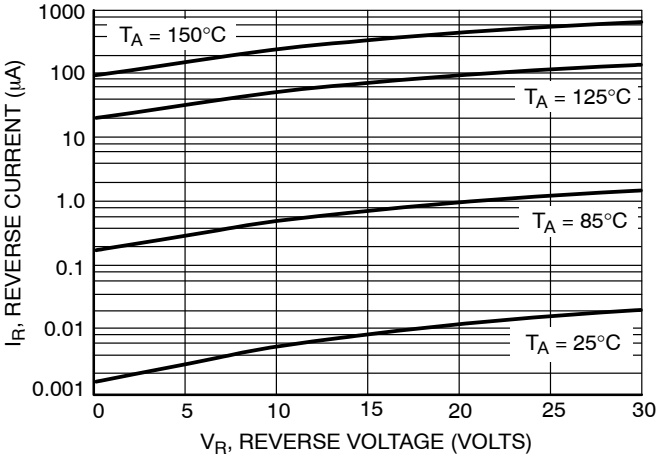


Figure 3. Leakage Current

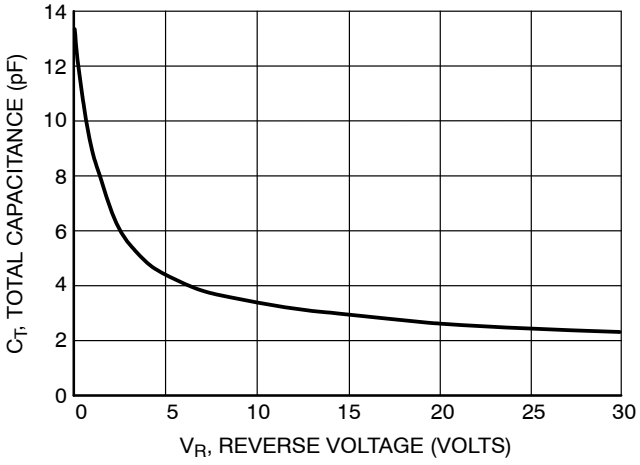
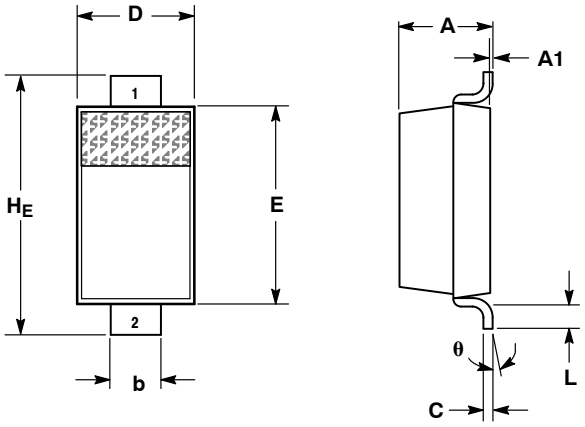


Figure 4. Total Capacitance

PACKAGE DIMENSIONS

SOD−123
CASE 425−04
ISSUE G

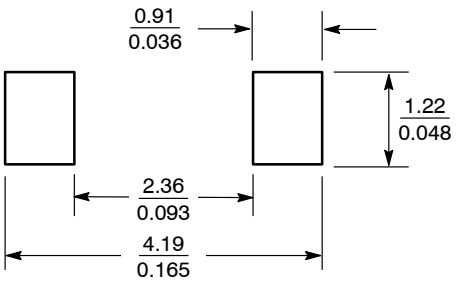


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.94	1.17	1.35	0.037	0.046	0.053
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.51	0.61	0.71	0.020	0.024	0.028
c	---	---	0.15	---	---	0.006
D	1.40	1.60	1.80	0.055	0.063	0.071
E	2.54	2.69	2.84	0.100	0.106	0.112
H_E	3.56	3.68	3.86	0.140	0.145	0.152
L	0.25	---	---	0.010	---	---
θ	0°	---	10°	0°	---	10°

STYLE 1:
PIN 1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
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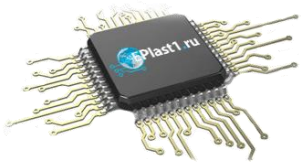
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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